

IN THE CLAIMS:

Please amend claims 1, 3-6, 8-11, 13-16, and 18-20 as follows:

B6 Sub C1 1. (Amended) An image sensor comprising:
an optical sensor formed over a substrate;
a thin film transistor electrically connected to said optical sensor in series; and
a capacitor having a first electrode and a second electrode, wherein said first electrode is electrically connected to said optical sensor between said optical sensor and said thin film transistor, and wherein said second electrode is at a ground potential.

D1 3. (Amended) An image sensor of claim 1 wherein a gate electrode of said thin film transistor is electrically connected to a shift register circuit.

B7 4. (Amended) An image sensor of claim 1 wherein said thin film transistor is electrically connected to a signal output terminal.

5. (Amended) An image sensor of claim 1 wherein said optical sensor comprises an amorphous semiconductor layer formed over a bottom gate type thin film transistor.

Sub C2 6. (Amended) An image sensor comprising:
an optical sensor formed over a substrate;
a thin film transistor electrically connected to said optical sensor in series;
a capacitor having a first electrode and a second electrode, wherein said first electrode is connected to said optical sensor between said optical sensor and said thin film transistor, and wherein said second electrode is at a ground potential ; and
an amplifier electrically connected to said thin film transistor in series.

8. (Amended) An image sensor of claim 6 wherein a gate electrode of said thin film transistor is electrically connected to at least one shift register circuit.

D1
9. (Amended) An image sensor of claim 6 wherein said amplifier is electrically connected to a signal output terminal.

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10. (Amended) An image sensor of claim 6 wherein said optical sensor comprises an amorphous semiconductor layer formed over a bottom gate type thin film transistor.

11. (Amended) An image sensor comprising:
a plurality of row lines and a plurality of column lines arranged in a matrix form over a substrate;

a plurality of thin film transistors formed over said substrate, a gate electrode of each of said thin film transistors being electrically connected to at least one of said plurality of row lines, and a first electrode of each of said thin film transistors being electrically connected to at least one of said plurality of column lines; and

a plurality of optical sensors formed over said substrate, a third electrode of each of said plurality of optical sensors being electrically connected to a second electrode of said each of said plurality of thin film transistors in series, and a fourth electrode of each of said plurality of optical sensors being electrically connected to a bias terminal.

13. (Amended) An image sensor of claim 11 wherein said plurality of row lines and said plurality of column lines are electrically connected to shift register circuits.

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14. (Amended) An image sensor of claim 11 wherein each of said plurality of column lines is electrically connected to a signal output terminal.

15. (Amended) An image sensor of claim 11 wherein said optical sensor comprises an amorphous semiconductor layer formed over a bottom gate type thin film transistor.

16. (Amended) An image sensor comprising:

a plurality of row lines and a plurality of column lines formed over a substrate;

B⁹ a plurality of thin film transistors formed over said substrate, a gate electrode of each of said thin film transistors being electrically connected to at least one of said plurality of row lines, and a first electrode of each of said thin film transistors being electrically connected to at least one of said plurality of column lines;

a plurality of optical sensors formed over said substrate, a third electrode of each of said plurality of optical sensors being electrically connected to a second electrode of said each of said plurality of thin film transistors in series, and a fourth electrode of each of said plurality of optical sensors being electrically connected to a bias terminal; and

a plurality of capacitors, each of said plurality of capacitors being electrically connected to said second electrode and said bias terminal, and being electrically connected to each of said plurality of optical sensors in parallel.

18. (Amended) An image sensor of claim 16 wherein said plurality of row lines and said plurality of column lines are electrically connected to shift register circuits.

B¹⁰ 19. (Amended) An image sensor of claim 16 wherein each of said plurality of column lines is electrically connected to a signal output terminal.

20. (Amended) An image sensor of claim 16 wherein said optical sensor comprises an amorphous semiconductor layer formed over a bottom gate type thin film transistor.
